ABSTRACT OF THE DISCLOSURE

In one implementation, first and second layers are formed over a substrate. One of the layers has a higher oxidation rate than the other when exposed to an oxidizing atmosphere. The layers respectively have an exposed outer edge spaced inside of the substrate periphery. Etching is conducted into the higher oxidation rate material at a faster rate than any etching which occurs into the lower oxidation rate material. Then, the substrate is exposed to the oxidizing atmosphere. In another implementation, a stack of at least two conductive layers for an electronic component is formed. The two conductive layers have different oxidation rates when exposed to an oxidizing atmosphere. The layer with the higher oxidation rate has an outer lateral edge which is recessed inwardly of a corresponding outer lateral edge of the layer with the lower oxidation rate. The stack is exposed to the oxidizing atmosphere effective to grow an oxide layer over the outer lateral edges of the first and second layers. In yet another implementation, a transistor comprises a semiconductive substrate and a gate stack formed thereover. The stack in at least one cross section defines a channel length within the substrate of less than 1 micron, with the stack comprising conductive material formed over a gate dielectric layer. An insulative layer is formed on outer lateral edges of the conductive material, with such layer having opposing substantially continuous straight linear outer lateral edges over all conductive material of the gate stack within the one cross section.